

PHASE CONTROL THYRISTORS

- Junction Size: Square 185 mils
- Wafer Size: 4"
- V_{RRM} Class: 1200 V
- Passivation Process: Glassivated MESA
- Reference IR Packaged Part: 25TTS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{TM} Maximum On-state Voltage	1.25 V	$T_J = 25^\circ\text{C}$, $I_T = 16\text{ A}$
V_{RRM} Reverse Breakdown Voltage	1200 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 100\text{ }\mu\text{A}$ (1)
I_{GT} Max. Required DC Gate Current to Trigger	60 mA	$T_J = 25^\circ\text{C}$, anode supply = 6 V, resistive load
V_{GT} Max. Required DC Gate Voltage to Trigger	2 V	$T_J = 25^\circ\text{C}$, anode supply = 6 V, resistive load
I_H Holding Current Range	5 to 100 mA	Anode supply = 6 V, resistive load
I_L Maximum Latching Current	200 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	185x185 mils (see drawing)
Wafer Diameter	100 mm, with std. <110> flat
Wafer Thickness	350 $\mu\text{m} \pm 10\text{ }\mu\text{m}$
Maximum Width of Sawing Line	130 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR185BG12DCB

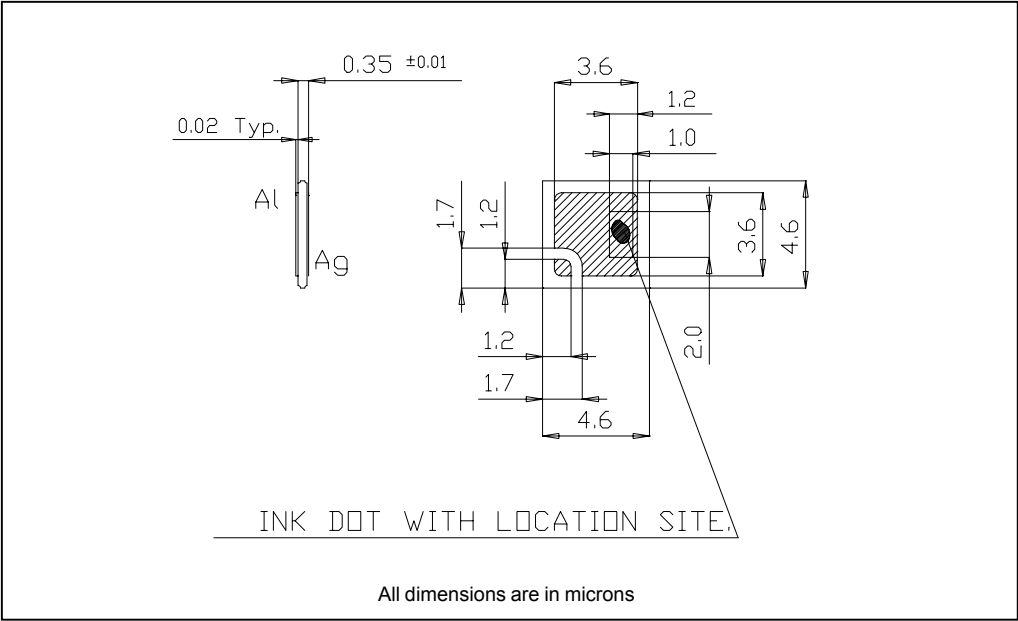
Bulletin I0202J rev. B 09/99



Ordering Information Table

Device Code						
IR	185	B	G	12	D	CB
1	2	3	4	5	6	7
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: B = Wire Bondable SCR					
4	- Passivation Process: G = Glassivated MESA					
5	- Voltage code: Code x 100 = V_{RRM}					
6	- Metallization: D = Silver (Anode) - Aluminium (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

Outline Table



Wafer Layout

